SG	PARAMETER	SYMBOL	TEMP.	POWER	TEST CONDITIONS	MIN	MAX	UNITS
1	Quiescent Current	I_Q	25°C	±32V	$V_{IN} = 0$, $A_V = 100$		10	mA
1	Input Offset Voltage	V_{OS}	25°C	±32V	$V_{IN} = 0$, $A_V = 100$		±6	mV
1	Input Offset Voltage	V_{OS}	25°C	±10V	$V_{IN} = 0$, $A_V = 100$		±10.4	mV
1	Input Offset Voltage	V_{OS}	25°C	±45V	$V_{IN} = 0$, $A_V = 100$		±8.6	mV
1	Input Bias Current, +IN	$+I_B$	25°C	±32V	$V_{IN} = 0$		±30	nA
1	Input Bias Current, −IN	$-I_B$	25°C	±32V	$V_{IN} = 0$		±30	nA
1	Input Offset Current	I_{OS}	25°C	±32V	$V_{IN} = 0$		±30	nA
3	Quiescent Current	I_Q	−55°C	±32V	$V_{IN} = 0$, $A_V = 100$		10	mA
3	Input Offset Voltage	V_{OS}	−55°C	±32V	$V_{IN} = 0$, $A_V = 100$		±11.2	mV
3	Input Offset Voltage	V_{OS}	−55°C	±10V	$V_{IN} = 0$, $A_V = 100$		±15.6	mV
3	Input Offset Voltage	V_{OS}	−55°C	±45V	$V_{IN} = 0$, $A_V = 100$		±13.8	mV
3	Input Bias Current, +IN	$+I_B$	−55°C	±32V	$V_{IN} = 0$		±115	nA
3	Input BiasCurrent, −IN	$-I_B$	−55°C	±32V	$V_{IN} = 0$		±115	nA
3	Input Offset Current	I_{OS}	−55°C	±32V	$V_{IN} = 0$		±115	nA
2	Quiescent Current	I_Q	125°C	±32V	$V_{IN} = 0$, $A_V = 100$		15	mA
2	Input Offset Voltage	V_{OS}	125°C	±32V	$V_{IN} = 0$, $A_V = 100$		±12.5	mV
2	Input Offset Voltage	V_{OS}	125°C	±10V	$V_{IN} = 0$, $A_V = 100$		±16.9	mV
2	Input Offset Voltage	V_{OS}	125°C	±45V	$V_{IN} = 0$, $A_V = 100$		±15.1	mV
2	Input Bias Current, +IN	$+I_B$	125°C	±32V	$V_{IN} = 0$		±70	nA
2	Input Bias Current, −IN	$-I_B$	125°C	±32V	$V_{IN} = 0$		±70	nA
2	Input Offset Current	I_{OS}	125°C	±32V	$V_{IN} = 0$		±70	nA
4	Output Voltage, $I_O = 10A$	V_O	25°C	±17V	$R_L = 1\Omega$	10		V
4	Output Voltage, $I_O = 80mA$	V_O	25°C	±45V	$R_L = 500\Omega$	40		V
4	Output Voltage, $I_O = 4A$	V_O	25°C	± 30V	$R_L = 6\Omega$	24		V
4	Current Limits	I_{CL}	25°C	±15V	$R_L = 6\Omega$, $R_{CL} = 1\Omega$	.56	.88	A
4	Stability/Noise	E_N	25°C	±32V	$R_L = 500\Omega$, $A_V = 1$, $C_L = 10nF$		1	mV
4	Slew Rate	SR	25°C	±32V	$R_L = 500\Omega$	1	10	V/µs
4	Open Loop Gain	A_{OL}	25°C	±32V	$R_L = 500\Omega$, $F = 10Hz$	96		dB
4	Common Mode Rejection	CMR	25°C	±15V	$R_L = 500\Omega$, $F = DC$, $V_{CM} = ±9V$	74		dB
6	Output Voltage, $I_O = 10A$	V_O	−55°C	±17V	$R_L = 1\Omega$	10		V
6	Output Voltage, $I_O = 80mA$	V_O	−55°C	±45V	$R_L = 500\Omega$	40		V
6	Output Voltage, $I_O = 4A$	V_O	−55°C	±30V	$R_L = 6\Omega$	24		V
6	Stability/Noise	E_N	−55°C	±32V	$R_L = 500\Omega$, $A_V = 1$, $C_L = 10nF$		1	mV
6	Slew Rate	SR	−55°C	±32V	$R_L = 500\Omega$	1	10	V/µs
6	Open Loop Gain	A_{OL}	−55°C	±32V	$R_L = 500\Omega$, $F = 10Hz$	96		dB
6	CommonMode Rejection	CMR	−55°C	±15V	$R_L = 500\Omega$, $F = DC$, $V_{CM} = ±9V$	74		dB
5	Output Voltage, $I_O = 8A$	V_O	125°C	±15V	$R_L = 1\Omega$	8		V
5	Output Voltage, $I_O = 80mA$	V_O	125°C	±45V	$R_L = 500\Omega$	40		V
5	Output Voltage, $I_O = 4A$	V_O	125°C	±30V	$R_L = 6\Omega$	24		V
5	Stability/Noise	E_N	125°C	±32V	$R_L = 500\Omega$, $A_V = 1$, $C_L = 10nF$		1	mV
5	Slew Rate	SR	125°C	±32V	$R_L = 500\Omega$	1	10	V/µs
5	Open Loop Gain	A_{OL}	125°C	±32V	$R_L = 500\Omega$, $F = 10Hz$	96		dB
5	Common Mode Rejection	CMR	125°C	±15V	$R_L = 500\Omega$, $F = DC$, $V_{CM} = ±9V$	74		dB

BURN IN CIRCUIT
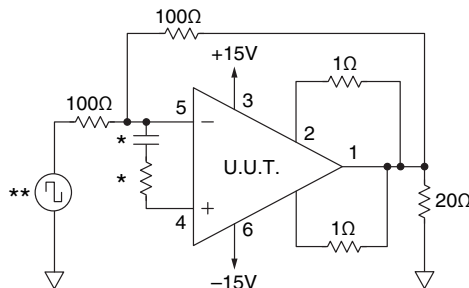
*   These components are used to stabilize device due to poor high frequency characteristics of burn in board.

**   Input signals are calculated to result in internal power dissipation of approximately 2.1W at case temperature = 125°C.